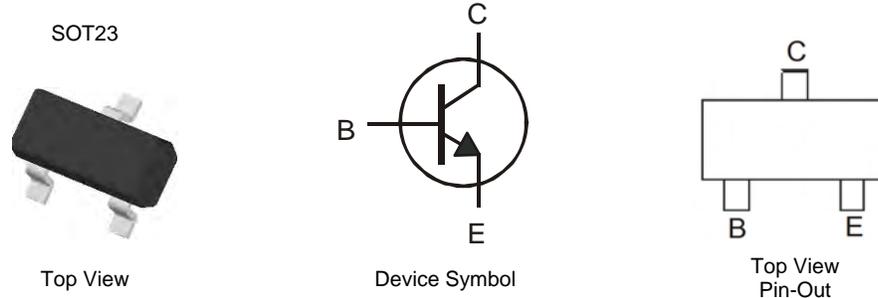


**40V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR**
**Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT3906)
- Ideal for Medium Power Amplification and Switching
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

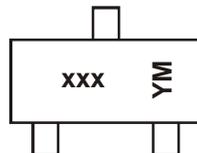
**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound,
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)


**Ordering Information** (Notes 4 & 5)

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3904-7-F	Commercial	K1N / C1N	7	8	3,000
MMBT3904Q-7-F	Automotive	K1N	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
  3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com>
  5. Products with Q-suffix are automotive grade. Automotive products are electrical and thermal the same as the commercial, except where specified.

**Marking Information**


Product Type Marking Code:  
 xxx = K1N or C1N  
 YM = Date Code Marking  
 Y = Year (ex: X = 2010)  
 M = Month (ex: 9 = September)

**Date Code Key**

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

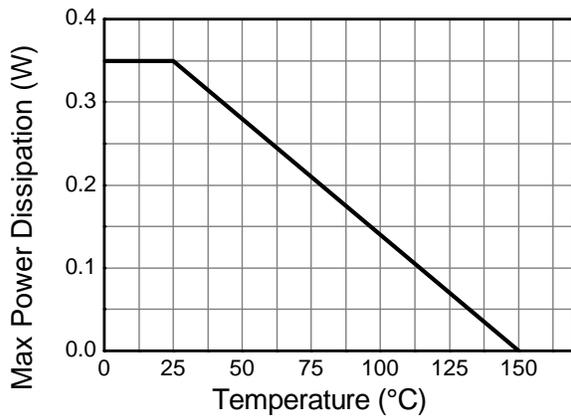
**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current - Continuous	I <sub>C</sub> (Note 7)	200	mA

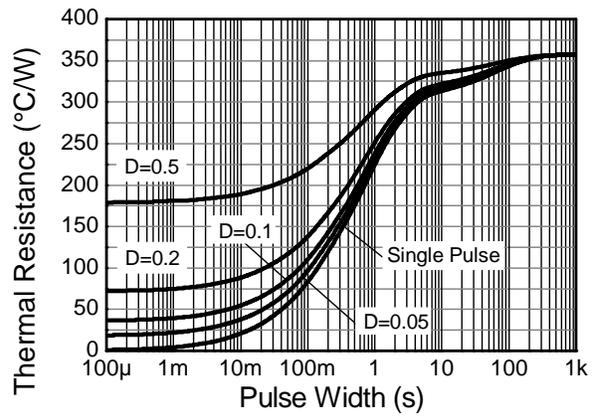
**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector Power Dissipation (Note 6)	P <sub>D</sub>	310	mW
(Note 7)		350	
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	403	°C/W
(Note 7)		357	
Thermal Resistance, Junction to Leads (Note 8)	R <sub>θJL</sub>	350	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

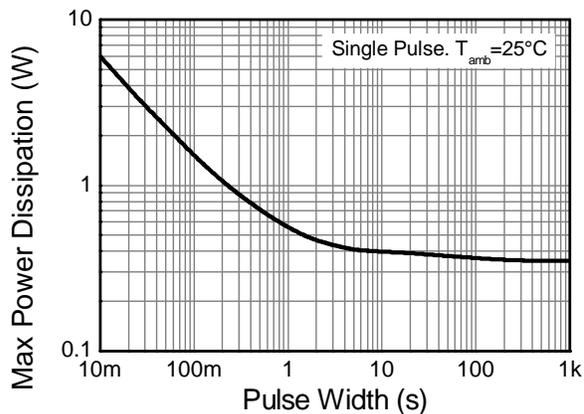
- Notes:
- 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  - 7. For the device mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  - 8. Thermal resistance from junction to solder-point (at the end of the collector lead).



**Derating Curve**



**Transient Thermal Impedance**



**Pulse Power Dissipation**

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	$BV_{CBO}$	60	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	$BV_{CEO}$	40	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CEX}$	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Base Cutoff Current	$I_{BL}$	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
<b>ON CHARACTERISTICS (Note 9)</b>					
DC Current Gain	$h_{FE}$	40	—	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}$
		70	—		
		100	300		
		60	—		
		30	—		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.65 —	0.85 0.95	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	4.0	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	$C_{ibo}$	—	8.0	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	$h_{ie}$	1.0	10	$k\Omega$	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA},$ $f = 1.0\text{kHz}$
Voltage Feedback Ratio	$h_{re}$	0.5	8.0	$\times 10^{-4}$	
Small Signal Current Gain	$h_{fe}$	100	400	—	
Output Admittance	$h_{oe}$	1.0	40	$\mu\text{S}$	
Current Gain-Bandwidth Product	$f_T$	300	—	MHz	$V_{CE} = 20\text{V}, I_C = 10\text{mA},$ $f = 100\text{MHz}$
Noise Figure	NF	—	5.0	dB	$V_{CE} = 5.0\text{V}, I_C = 100\mu\text{A},$ $R_S = 1.0k\Omega, f = 1.0\text{kHz}$
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	$t_d$	—	35	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA},$ $V_{BE(off)} = -0.5\text{V}, I_{B1} = 1.0\text{mA}$
Rise Time	$t_r$	—	35	ns	
Storage Time	$t_s$	—	200	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA},$ $I_{B1} = I_{B2} = 1.0\text{mA}$
Fall Time	$t_f$	—	50	ns	

Notes: 9. Short duration pulse test used to minimize self-heating effect.

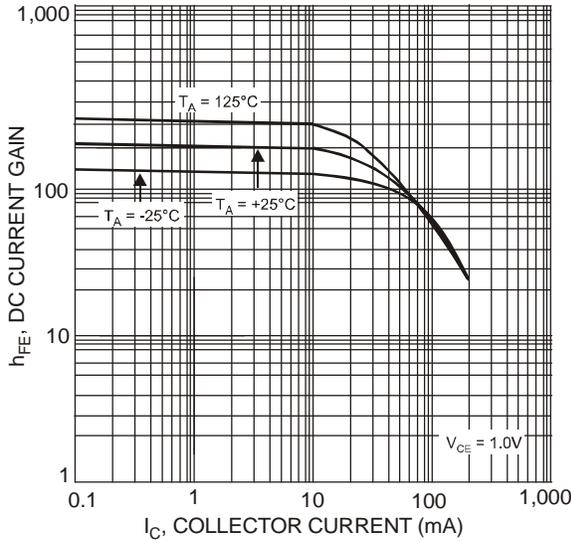


Fig. 1 Typical DC Current Gain vs. Collector Current

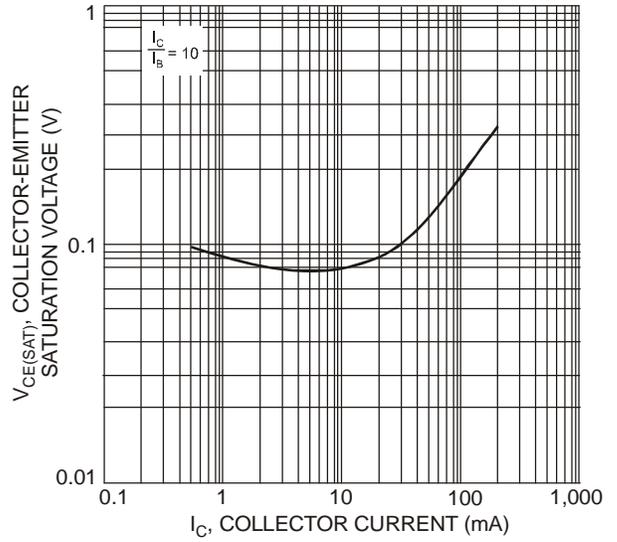


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

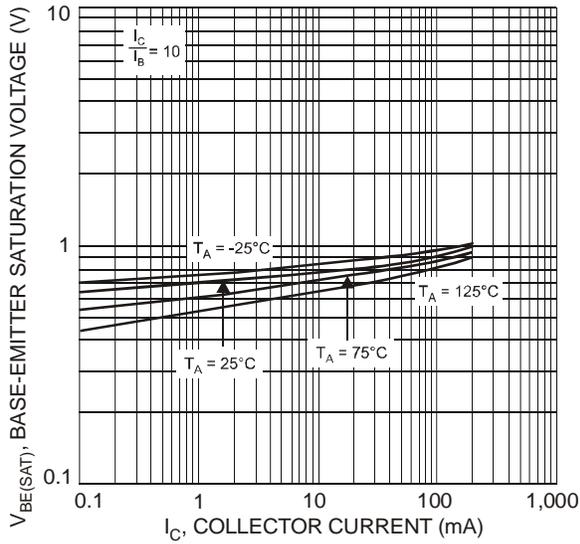


Fig. 3 Typical Base-Emitter Saturation Voltage vs. Collector Current

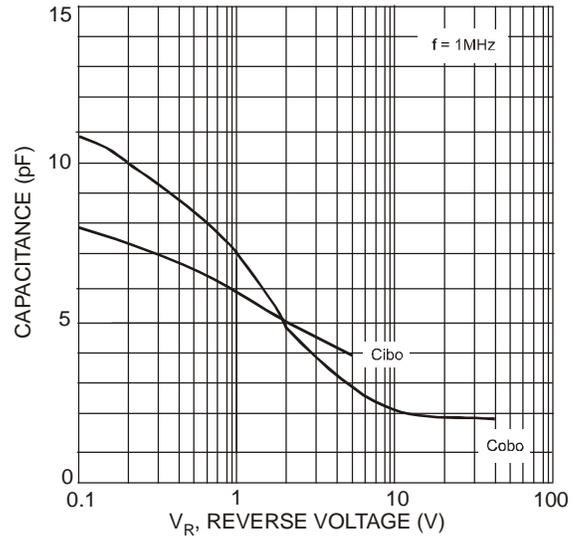


Fig. 4 Typical Capacitance Characteristics

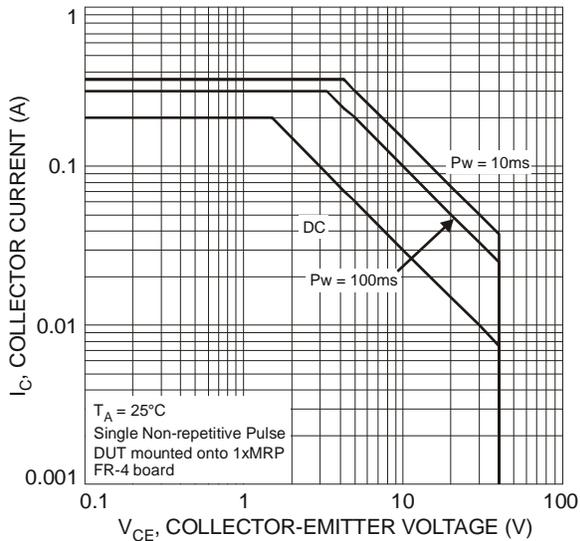
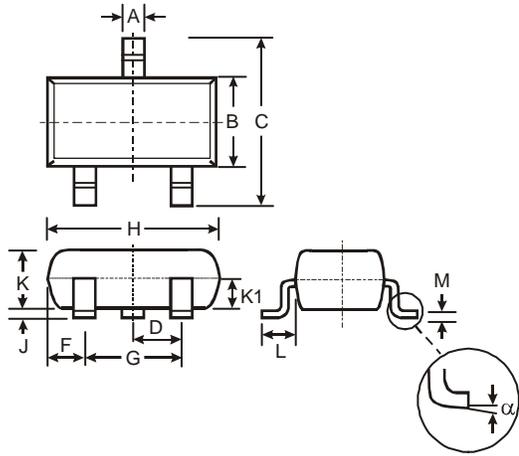


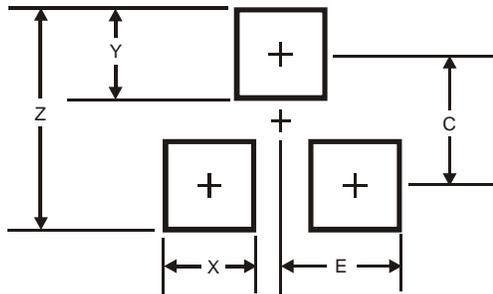
Fig. 5 Typical Collector Current vs. Collector-Emitter Voltage

**Package Outline Dimensions**



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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